



REPLACEMENT SHEET

1/22

FIG. 1A

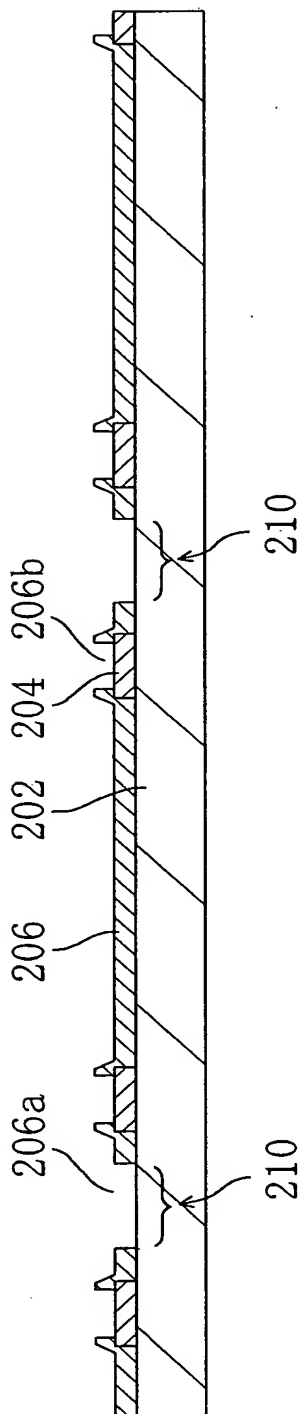


FIG. 1B

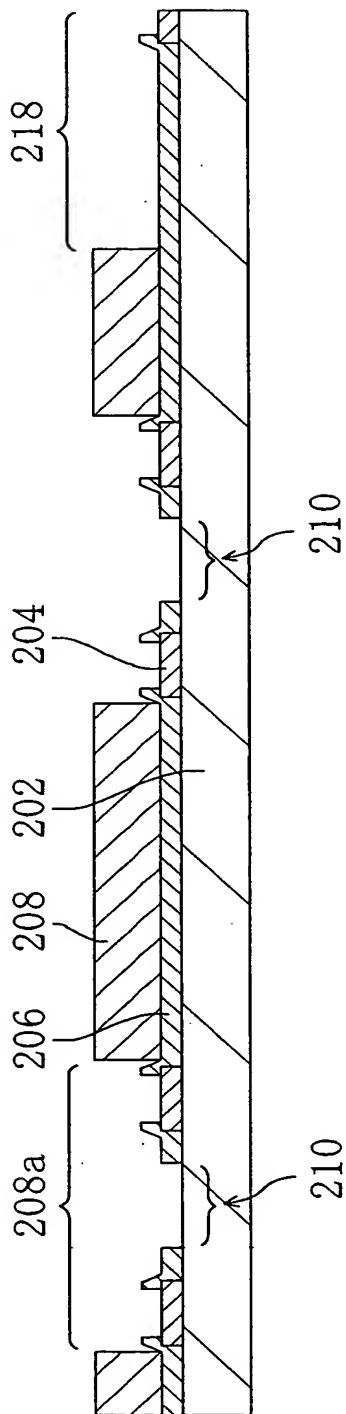


FIG. 2A

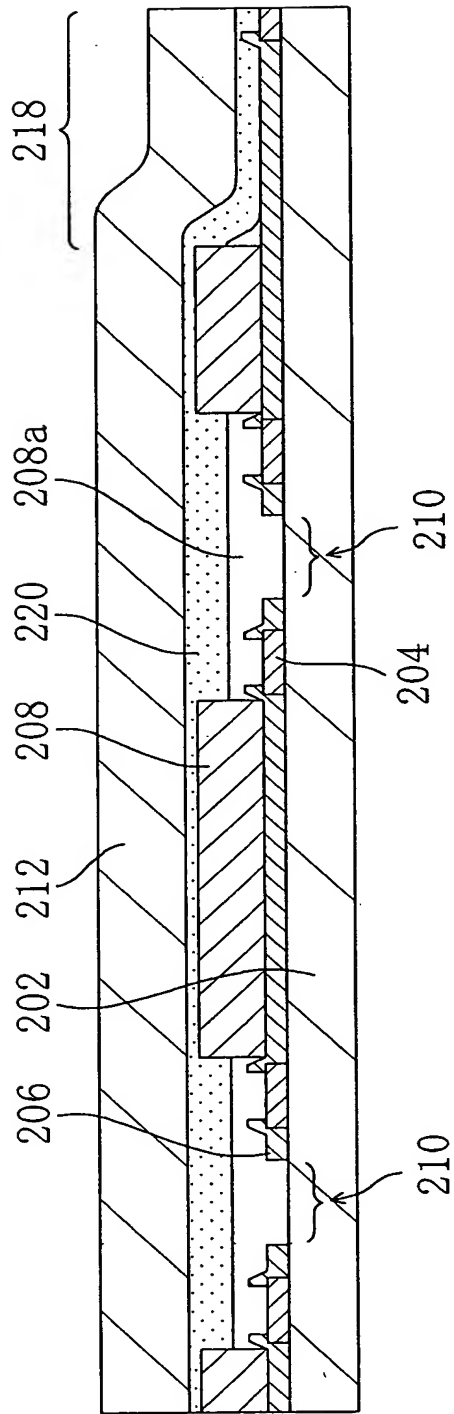


FIG. 2B

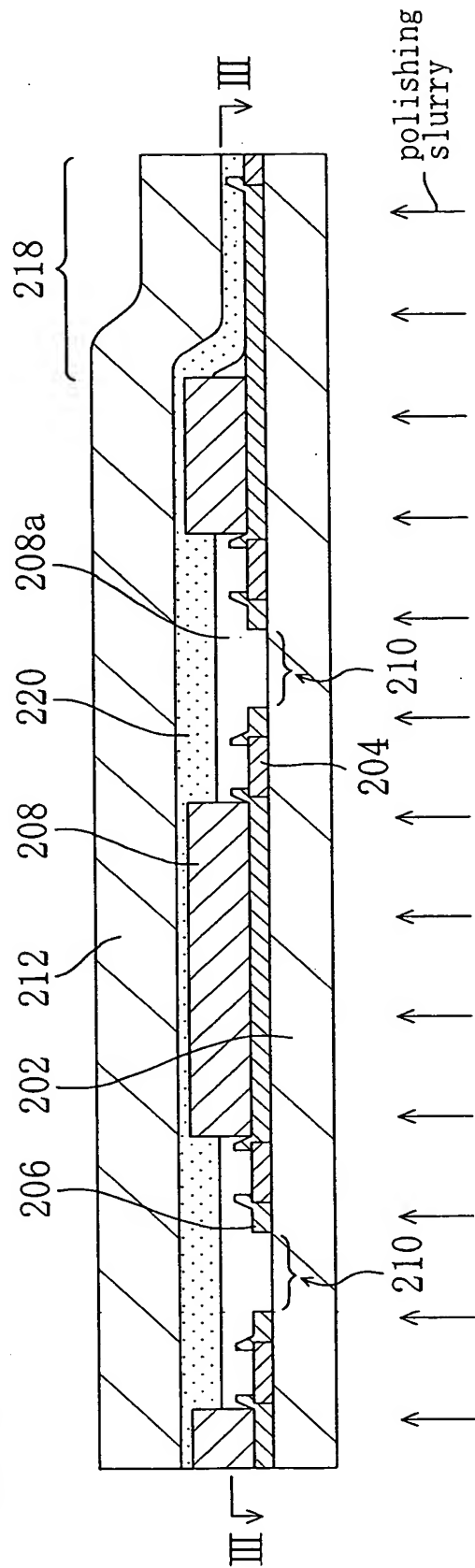


FIG. 4A

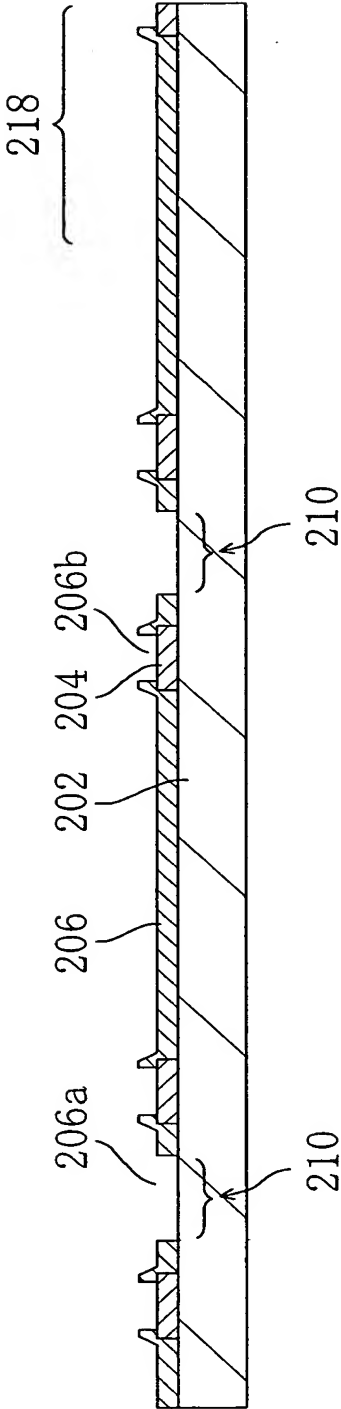


FIG. 4B

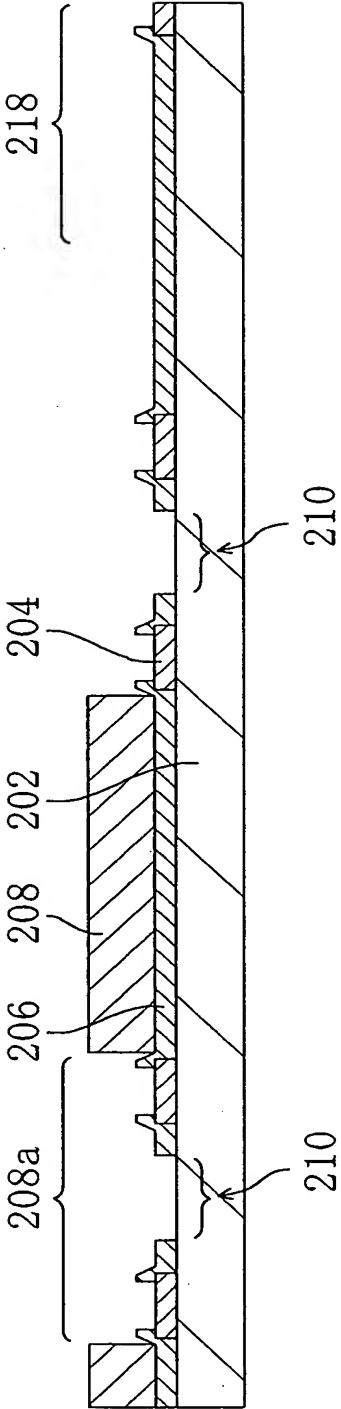


FIG. 5A

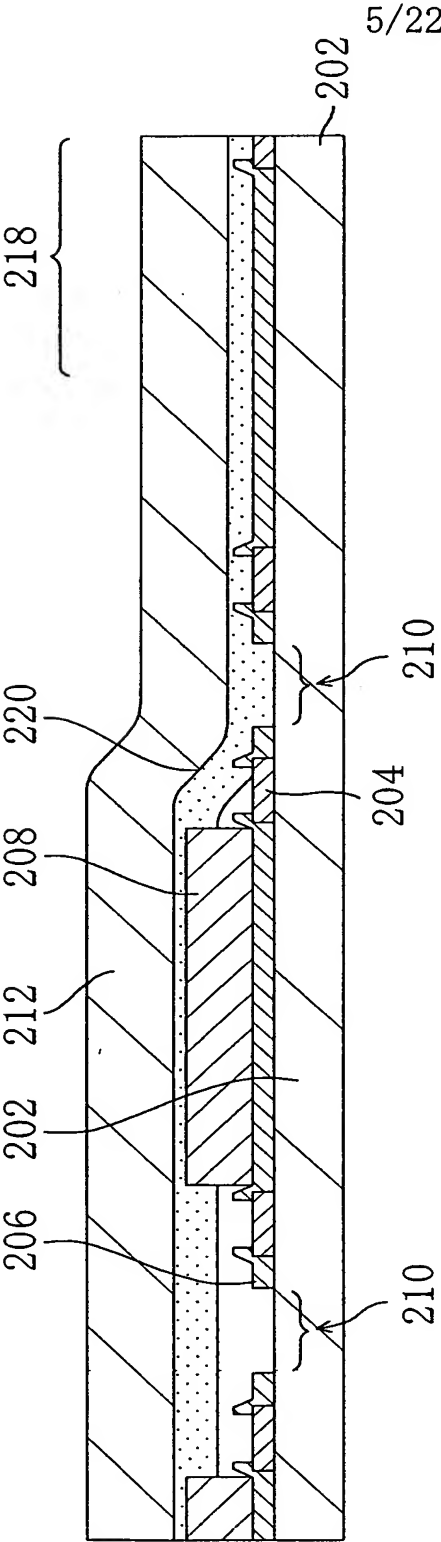


FIG. 5B

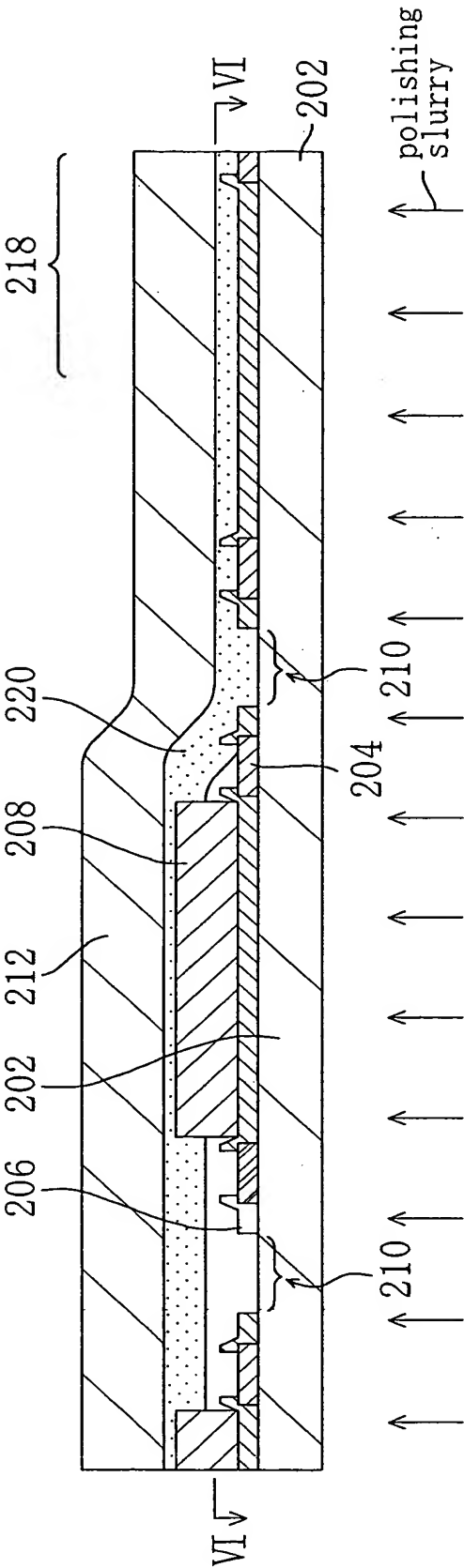


FIG. 7A

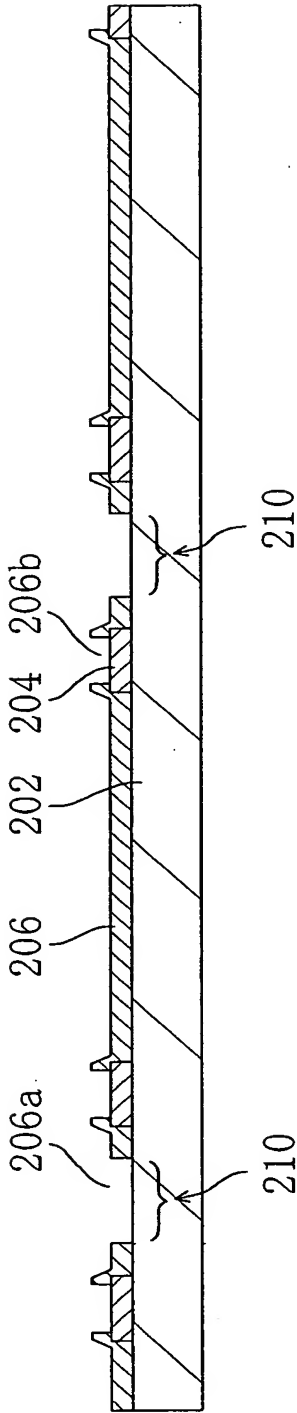
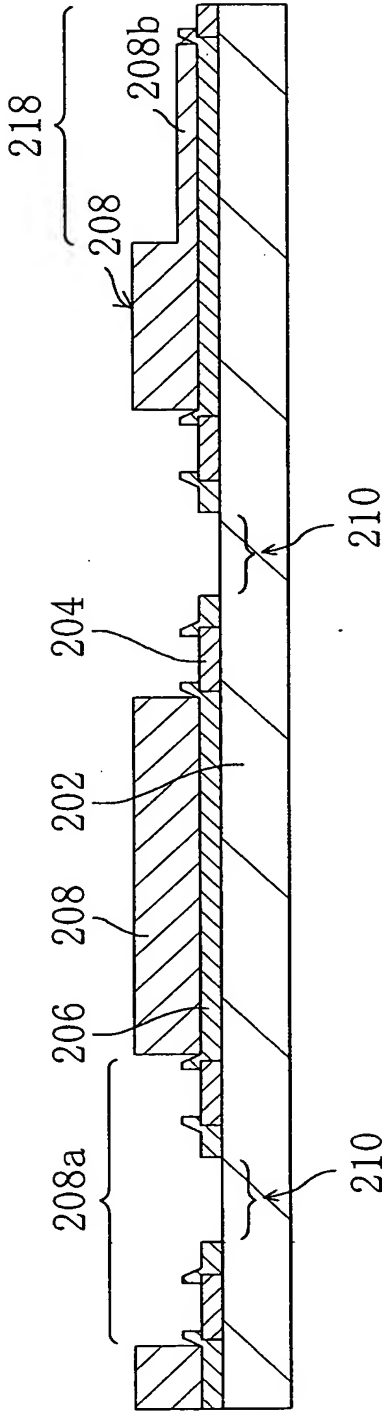


FIG. 7B



8/22

FIG. 8A

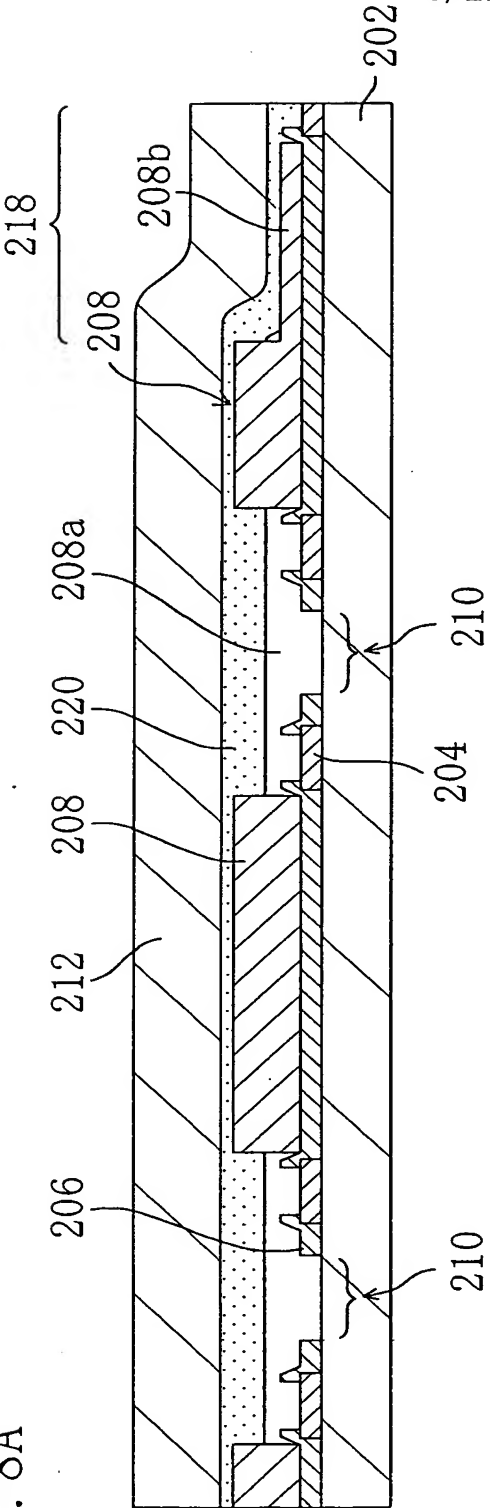


FIG. 8B

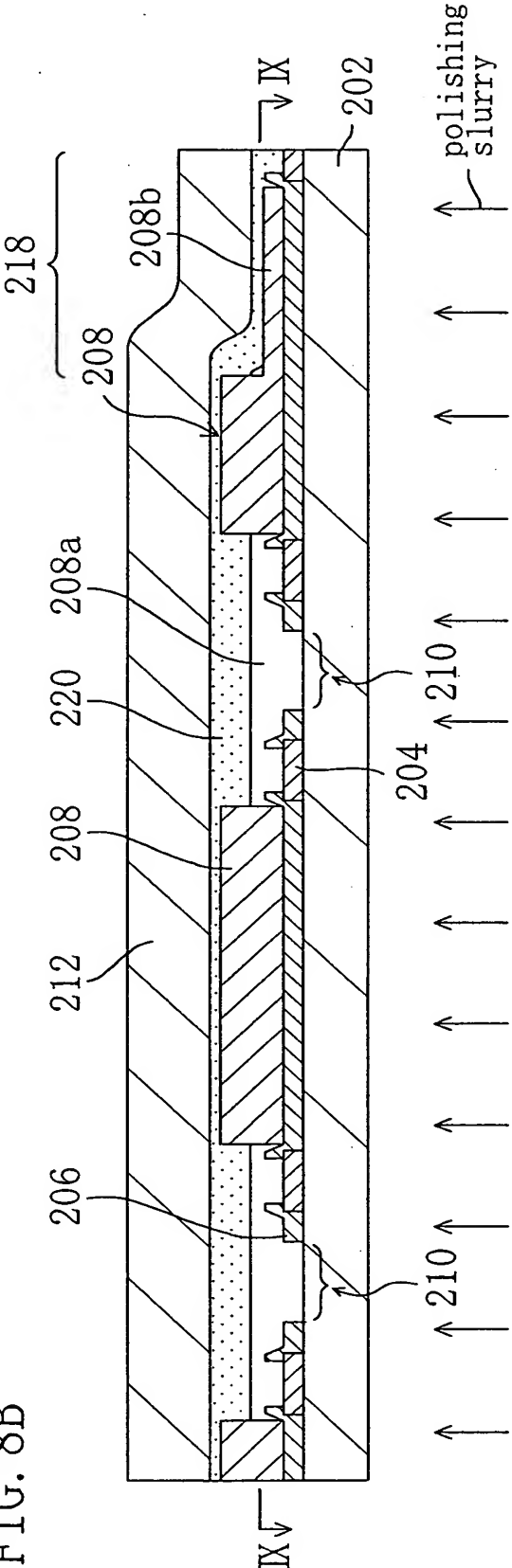


FIG. 10A

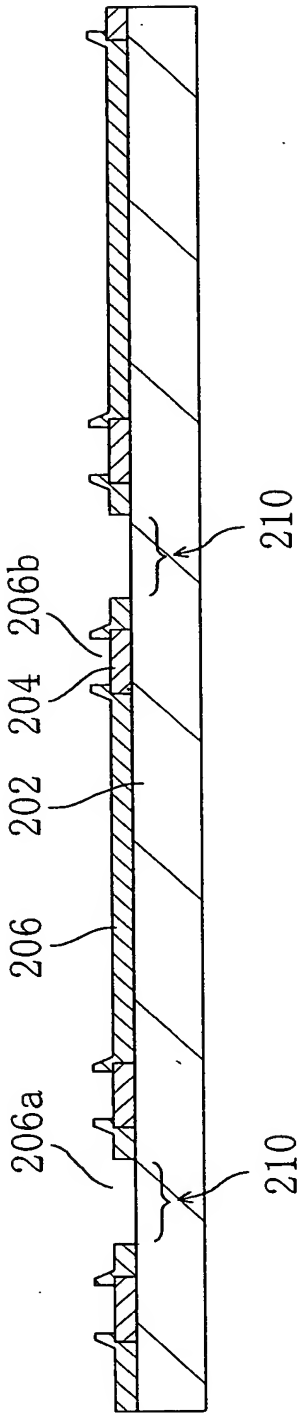
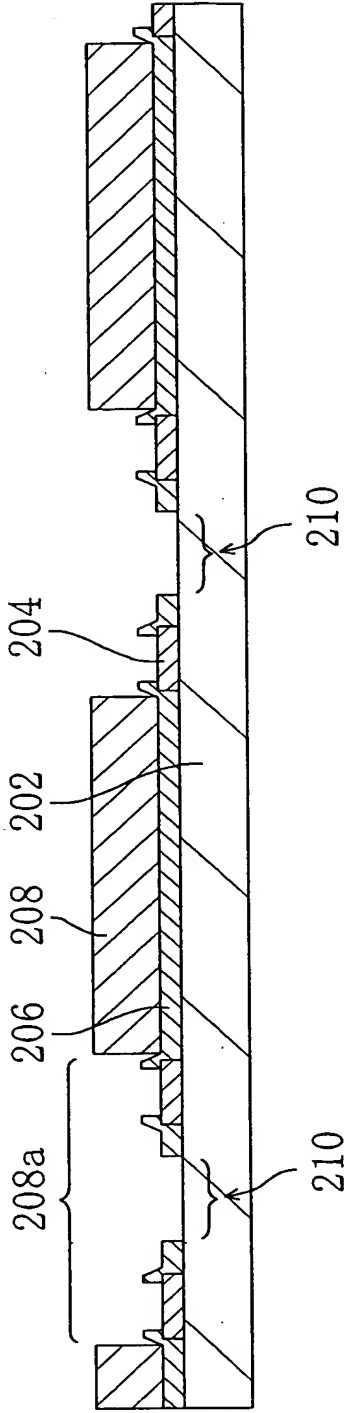


FIG. 10B



11/22

FIG. 11A

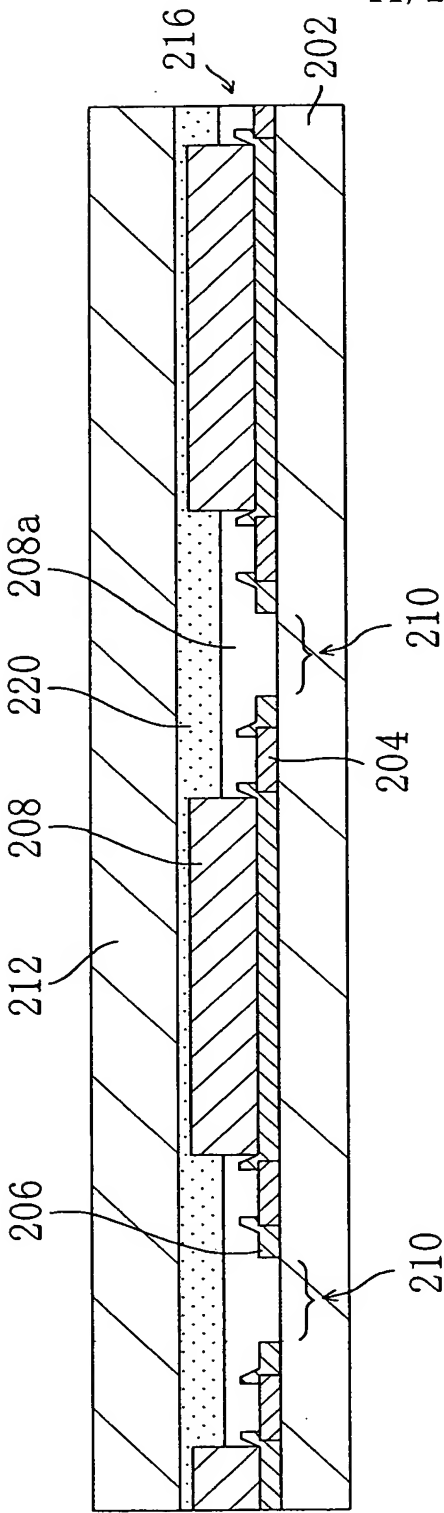


FIG. 11B

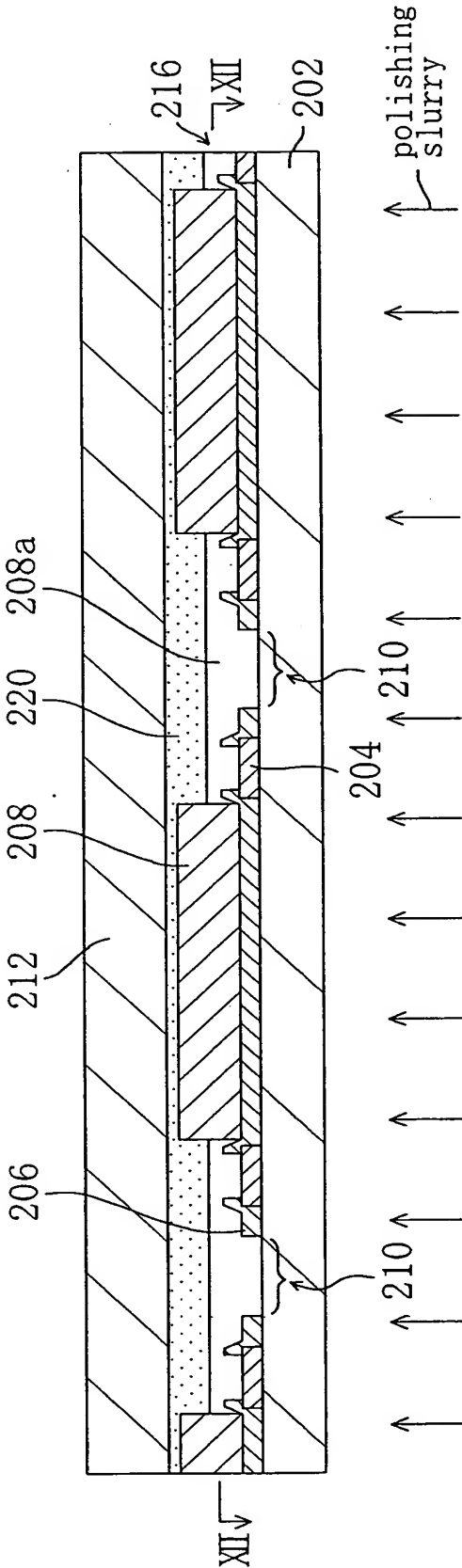


FIG. 13A

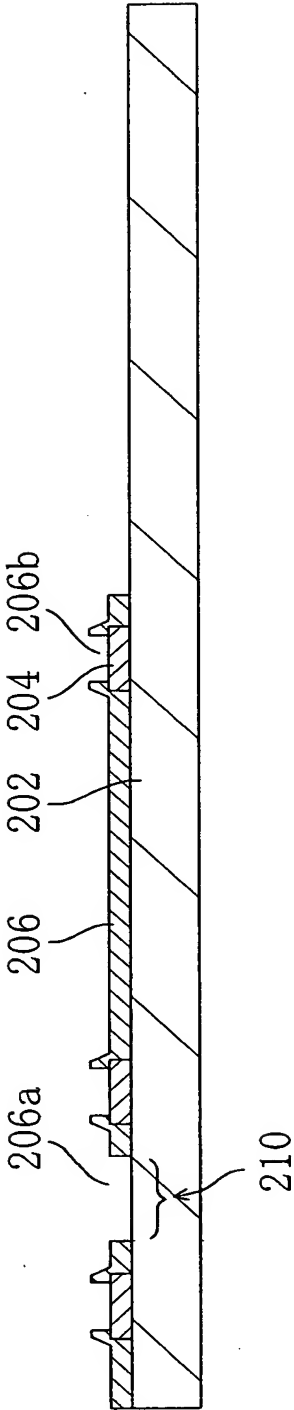
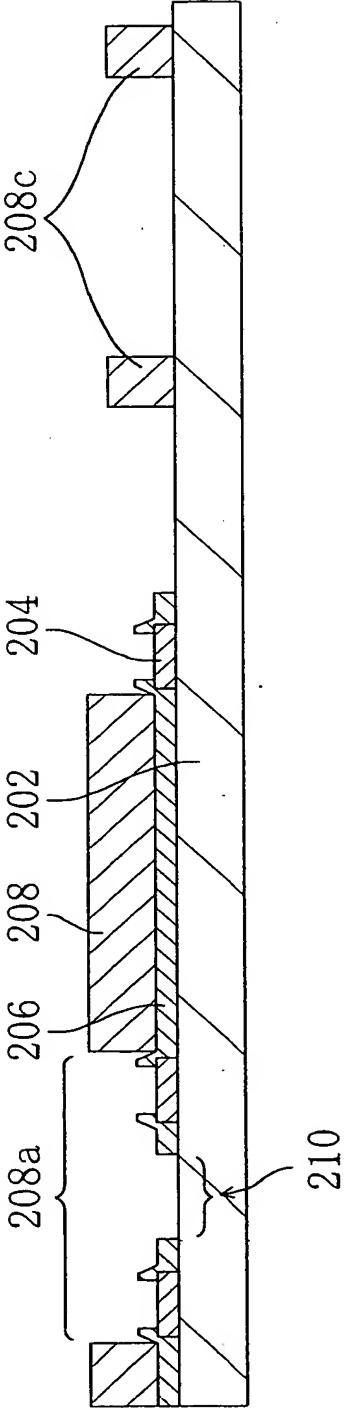


FIG. 13B



14/22

A cross-sectional view of a semiconductor device. The device consists of several layers. At the top is a layer labeled 202. Below it is a layer labeled 204. Underneath 204 is a layer labeled 206. Below 206 is a layer labeled 210. Within layer 210, there are several rectangular features labeled 212. Below 210 is a layer labeled 216. Underneath 216 is a layer labeled 220. At the bottom is a layer labeled 280. There are also features labeled 282, which appear to be small rectangular structures on the 216 layer. The layers 202, 204, 206, 210, 216, and 280 are shown with different hatching patterns to distinguish them.

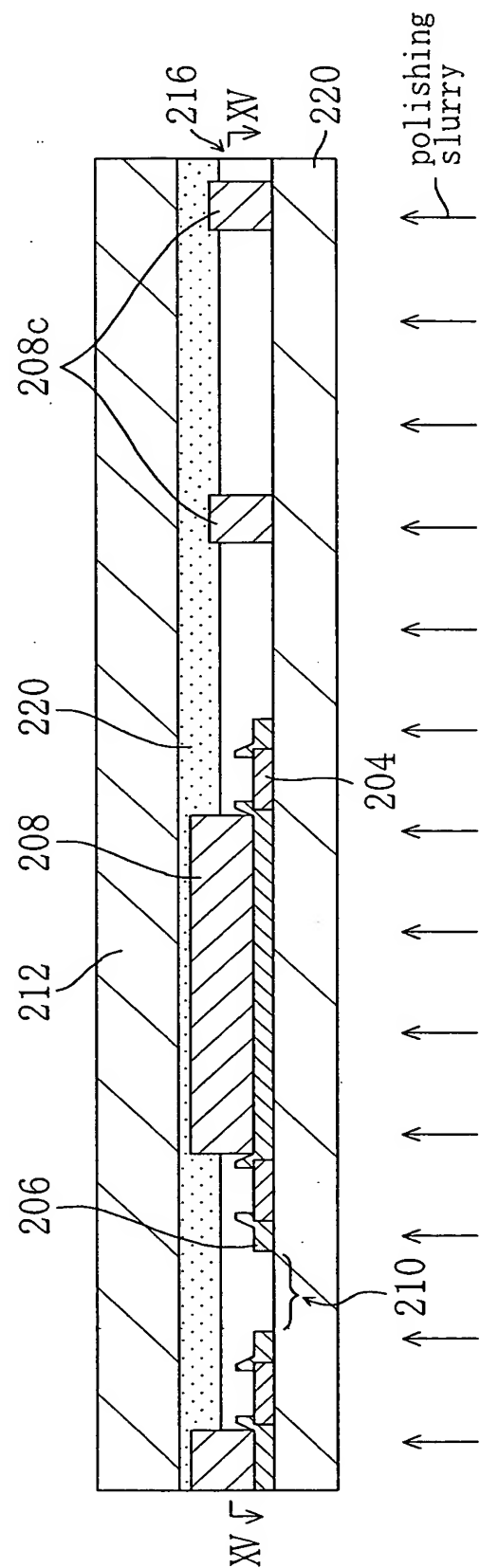


FIG. 16A

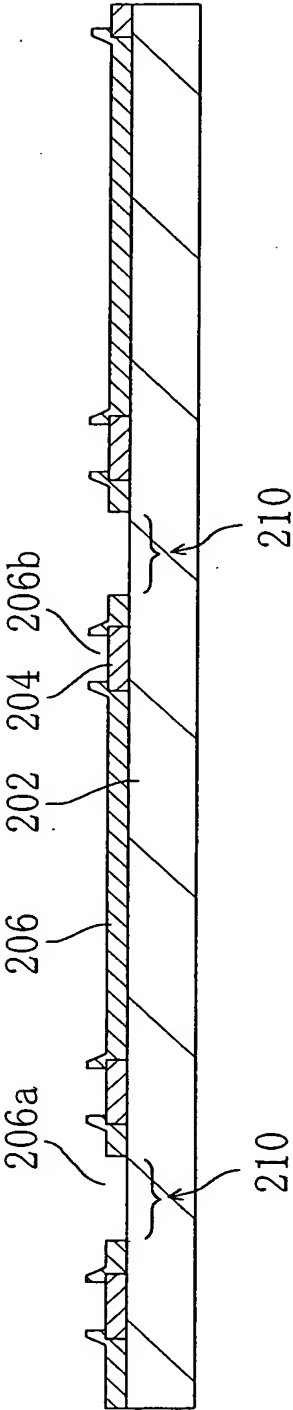


FIG. 16B

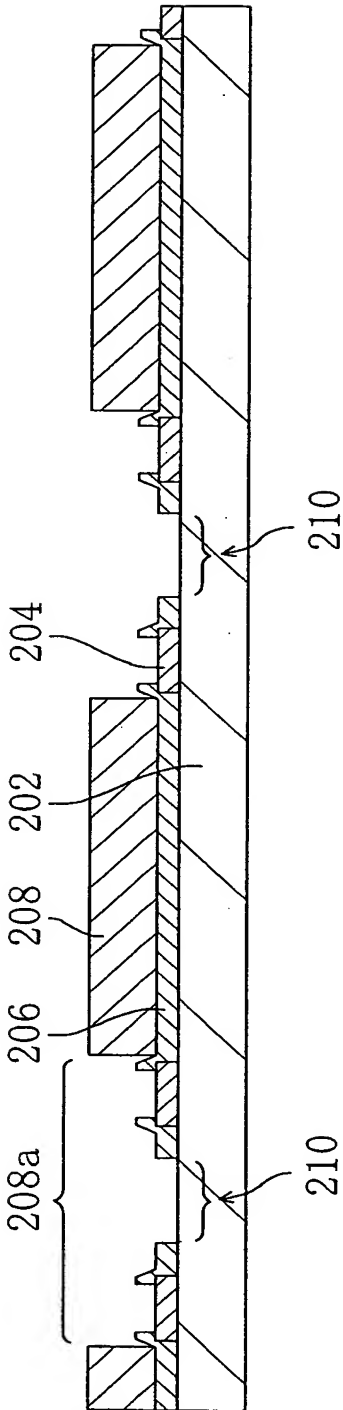


FIG. 17A

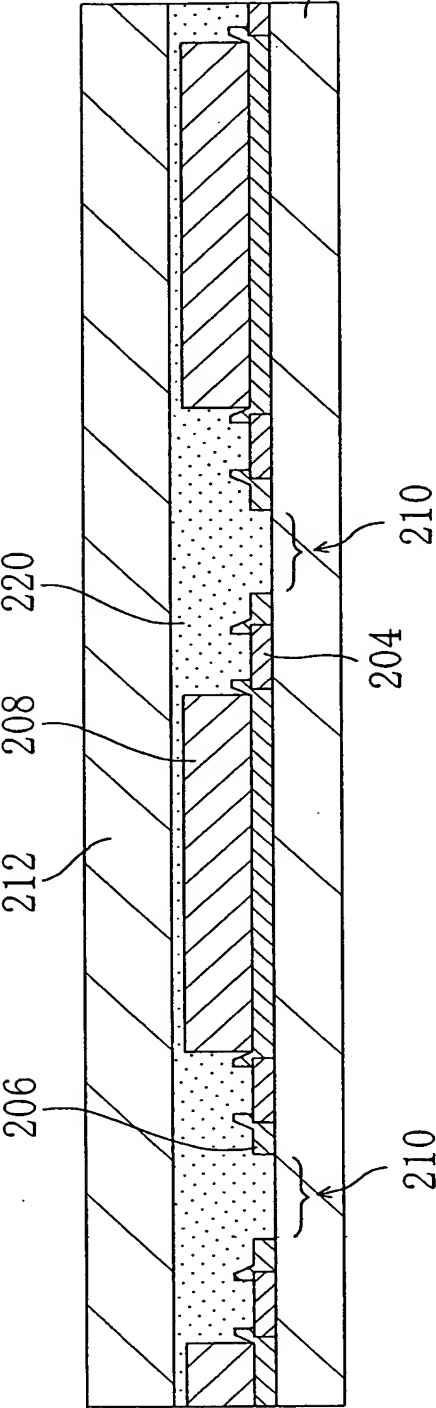


FIG. 17B

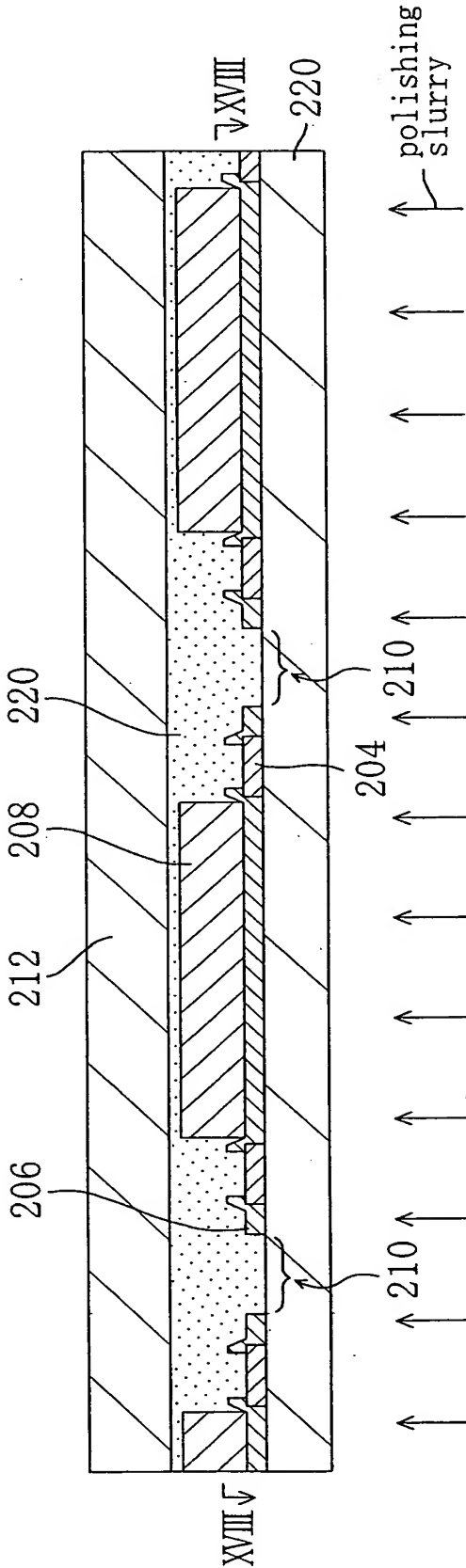


FIG. 20A
PRIOR ART

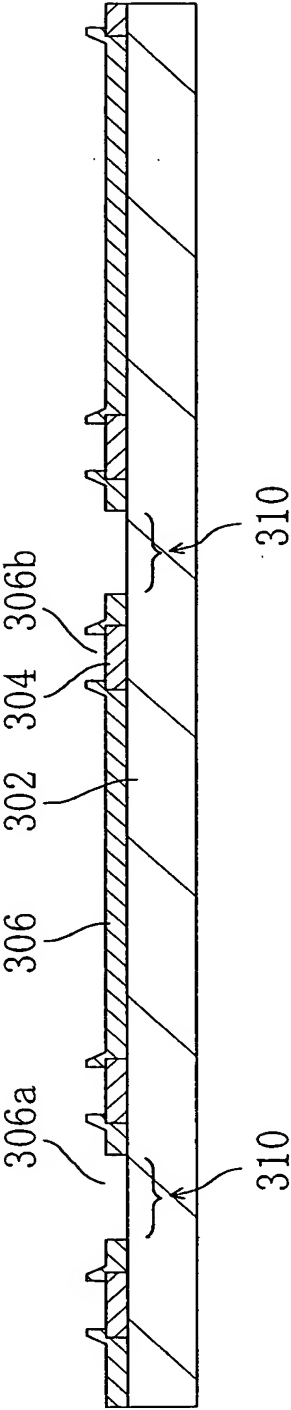


FIG. 20B
PRIOR ART

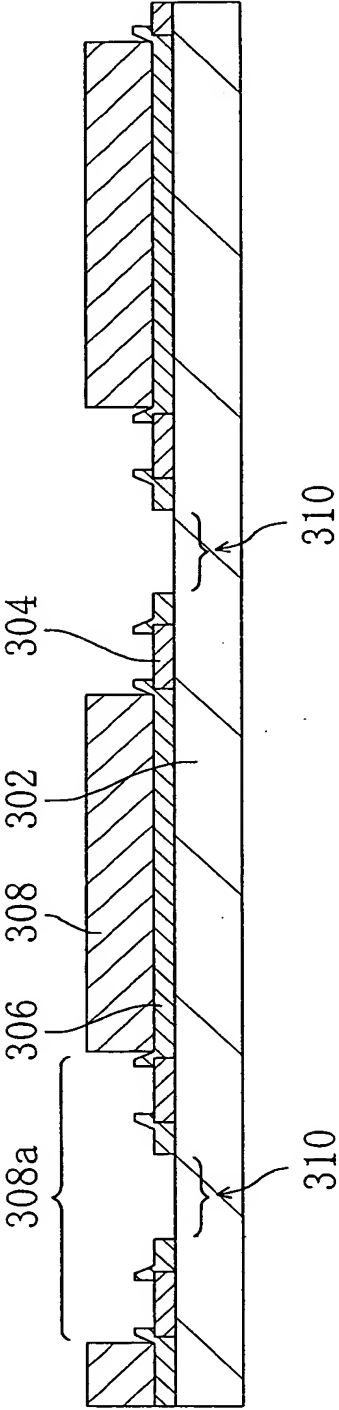


FIG. 21A
PRIOR ART

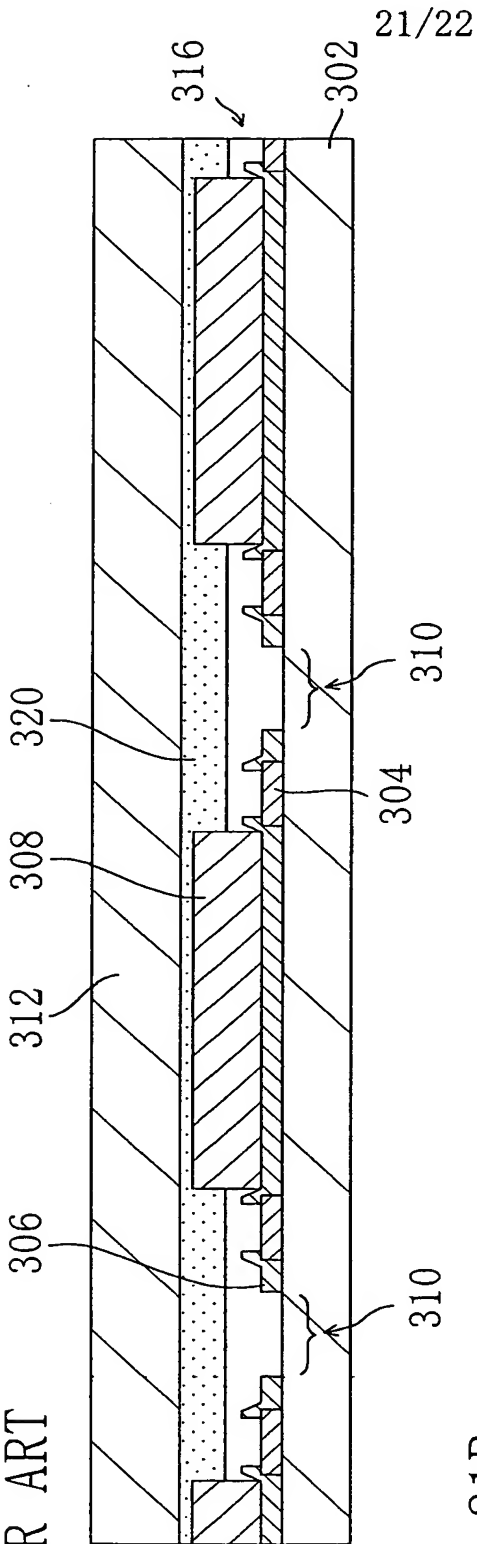


FIG. 21B
PRIOR ART

